NSN 5961-01-407-0040

Fiig: A110a0

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-407-0040 **Inclosure Material:** Ceramic and metal **Overall Length:** Between 0.130 inches and 0.146 inches Overall Diameter: Between 0.063 inches and 0.067 inches **Function For Which Designed:** Switching Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-213aa **Mounting Method:** Press fit **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 50.0 working peak reverse voltage **Current Rating Per Characteristic:** 33.00 milliamperes source cutoff current megahertz **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 case **Specification Data:** 81349-mil-s-19500/444 government specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** No